

3. (Amended) A semiconductor device comprising a TFT containing an active layer having a convex portion or a concave portion in a channel forming region, wherein the number of grain boundaries crossing the channel forming region in the width direction of the channel is zero or one.

10. (Amended) A semiconductor device according to any one of claims 1 to 3, wherein said semiconductor device is incorporated into an electronic device selected from the group consisting of a personal computer, a projector, a digital camera, a video camera, a head mounted display, a portable information terminal, a navigation system, a game machine, an image playback machine and a music playback machine.

Please add new claims 11-17:

--11. A semiconductor device comprising:
a semiconductor layer formed over a substrate; and
a channel forming region and source and drain regions formed in said semiconductor layer,
wherein said channel forming region has at least one convex portion.

12. A semiconductor device comprising:
a semiconductor layer formed over a substrate; and
a channel forming region and source and drain regions formed in said semiconductor layer,
wherein said channel forming region has at least one concave portion.

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13. A semiconductor device comprising:
a semiconductor layer formed over substrate; and
a channel forming region and source and drain regions formed in said semiconductor layer,
wherein said channel forming region has at least one convex portion in a channel width direction.

14. A semiconductor device comprising:
a semiconductor layer formed over a substrate; and
a channel forming region and source and drain regions formed in said semiconductor layer,
wherein said channel forming region has at least one concave portion in a channel width direction.

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15. A semiconductor device comprising:
a semiconductor layer formed over a substrate; and
a channel forming region and source and drain regions formed in said semiconductor layer,
wherein said channel forming region has at least one convex portion in a direction perpendicular to a carrier flow direction.

16. A semiconductor device comprising:
a semiconductor layer formed over a substrate;
a channel forming region and source and drain regions formed in said semiconductor layer; and
wherein said channel forming region has at least one concave portion in a direction perpendicular to a carrier flow direction.